

## OptiMOS™3 Power-Transistor

### Features

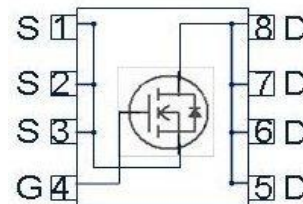
- Ideal for high frequency switching and sync. rec.
- Optimized technology for DC/DC converters
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Superior thermal resistance
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Halogen-free according to IEC61249-2-21

### Product Summary

|                  |    |    |
|------------------|----|----|
| $V_{DS}$         | 60 | V  |
| $R_{DS(on),max}$ | 11 | mΩ |
| $I_D$            | 50 | A  |



|         |                                                                                    |
|---------|------------------------------------------------------------------------------------|
| Type    | BSC110N06NS3 G                                                                     |
|         |  |
| Package | PG-TDSON-8                                                                         |
| Marking | 110N06NS                                                                           |



**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter                                    | Symbol        | Conditions                                                                   | Value | Unit |
|----------------------------------------------|---------------|------------------------------------------------------------------------------|-------|------|
| Continuous drain current                     | $I_D$         | $V_{GS}=10\text{ V}$ , $T_C=25\text{ °C}$                                    | 50    | A    |
|                                              |               | $V_{GS}=10\text{ V}$ , $T_C=100\text{ °C}$                                   | 33    |      |
|                                              |               | $V_{GS}=10\text{ V}$ , $T_C=25\text{ °C}$ ,<br>$R_{thJA}=50\text{ K/W}^{2)}$ | 12    |      |
| Pulsed drain current <sup>3)</sup>           | $I_{D,pulse}$ | $T_C=25\text{ °C}$                                                           | 200   |      |
| Avalanche energy, single pulse <sup>4)</sup> | $E_{AS}$      | $I_D=50\text{ A}$ , $R_{GS}=25\text{ Ω}$                                     | 22    | mJ   |
| Gate source voltage                          | $V_{GS}$      |                                                                              | ±20   | V    |

<sup>1)</sup> J-STD20 and JESD22

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

<sup>3)</sup> See figure 3 for more detailed information

<sup>4)</sup> See figure 13 for more detailed information

**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter                           | Symbol                | Conditions                                                    | Value       | Unit |
|-------------------------------------|-----------------------|---------------------------------------------------------------|-------------|------|
| Power dissipation                   | $P_{\text{tot}}$      | $T_C=25\text{ °C}$                                            | 50          | W    |
|                                     |                       | $T_A=25\text{ °C}$ ,<br>$R_{\text{thJA}}=50\text{ K/W}^{(2)}$ | 2.5         |      |
| Operating and storage temperature   | $T_j, T_{\text{stg}}$ |                                                               | -55 ... 150 | °C   |
| IEC climatic category; DIN IEC 68-1 |                       |                                                               | 55/150/56   |      |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

#### Thermal characteristics

|                                     |                   |                                               |   |   |     |     |
|-------------------------------------|-------------------|-----------------------------------------------|---|---|-----|-----|
| Thermal resistance, junction - case | $R_{\text{thJC}}$ |                                               | - | - | 2.5 | K/W |
| Device on PCB                       | $R_{\text{thJA}}$ | minimal footprint                             | - | - | 62  |     |
|                                     |                   | 6 cm <sup>2</sup> cooling area <sup>(2)</sup> | - | - | 50  |     |

**Electrical characteristics**, at  $T_j=25\text{ °C}$ , unless otherwise specified

#### Static characteristics

|                                  |                             |                                                                                       |    |     |     |               |
|----------------------------------|-----------------------------|---------------------------------------------------------------------------------------|----|-----|-----|---------------|
| Drain-source breakdown voltage   | $V_{(\text{BR})\text{DSS}}$ | $V_{\text{GS}}=0\text{ V}, I_{\text{D}}=1\text{ mA}$                                  | 60 | -   | -   | V             |
| Gate threshold voltage           | $V_{\text{GS(th)}}$         | $V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=23\text{ }\mu\text{A}$                     | 2  | 3   | 4   |               |
| Zero gate voltage drain current  | $I_{\text{DSS}}$            | $V_{\text{DS}}=60\text{ V}, V_{\text{GS}}=0\text{ V}$ ,<br>$T_j=25\text{ °C}$         | -  | 0.1 | 1   | $\mu\text{A}$ |
|                                  |                             | $V_{\text{DS}}=60\text{ V}, V_{\text{GS}}=0\text{ V}$ ,<br>$T_j=125\text{ °C}$        | -  | 10  | 100 |               |
| Gate-source leakage current      | $I_{\text{GSS}}$            | $V_{\text{GS}}=20\text{ V}, V_{\text{DS}}=0\text{ V}$                                 | -  | 10  | 100 | nA            |
| Drain-source on-state resistance | $R_{\text{DS(on)}}$         | $V_{\text{GS}}=10\text{ V}, I_{\text{D}}=50\text{ A}$                                 | -  | 9.0 | 11  | mΩ            |
| Gate resistance                  | $R_{\text{G}}$              |                                                                                       | -  | 1.3 | -   | Ω             |
| Transconductance                 | $g_{\text{fs}}$             | $ V_{\text{DS}} >2 I_{\text{D}} R_{\text{DS(on)max}}$ ,<br>$I_{\text{D}}=50\text{ A}$ | 25 | 50  | -   | S             |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic characteristics**

|                              |              |                                                                                     |   |      |      |    |
|------------------------------|--------------|-------------------------------------------------------------------------------------|---|------|------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=30\text{ V},$<br>$f=1\text{ MHz}$                        | - | 2000 | 2700 | pF |
| Output capacitance           | $C_{oss}$    |                                                                                     | - | 440  | 590  |    |
| Reverse transfer capacitance | $C_{rss}$    |                                                                                     | - | 17   | -    |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=30\text{ V}, V_{GS}=10\text{ V},$<br>$I_D=50\text{ A}, R_{G,ext}=3\ \Omega$ | - | 10   | -    | ns |
| Rise time                    | $t_r$        |                                                                                     | - | 77   | -    |    |
| Turn-off delay time          | $t_{d(off)}$ |                                                                                     | - | 14   | -    |    |
| Fall time                    | $t_f$        |                                                                                     | - | 6    | -    |    |

**Gate Charge Characteristics<sup>5)</sup>**

|                          |               |                                                                            |   |     |    |    |
|--------------------------|---------------|----------------------------------------------------------------------------|---|-----|----|----|
| Gate to source charge    | $Q_{gs}$      | $V_{DD}=30\text{ V}, I_D=50\text{ A},$<br>$V_{GS}=0\text{ to }10\text{ V}$ | - | 12  | -  | nC |
| Gate charge at threshold | $Q_{g(th)}$   |                                                                            | - | 6   | -  |    |
| Gate to drain charge     | $Q_{gd}$      |                                                                            | - | 3   | -  |    |
| Switching charge         | $Q_{sw}$      |                                                                            | - | 8   | -  |    |
| Gate charge total        | $Q_g$         |                                                                            | - | 25  | 33 |    |
| Gate plateau voltage     | $V_{plateau}$ |                                                                            | - | 5.9 | -  | V  |
| Output charge            | $Q_{oss}$     | $V_{DD}=30\text{ V}, V_{GS}=0\text{ V}$                                    | - | 20  | 27 |    |

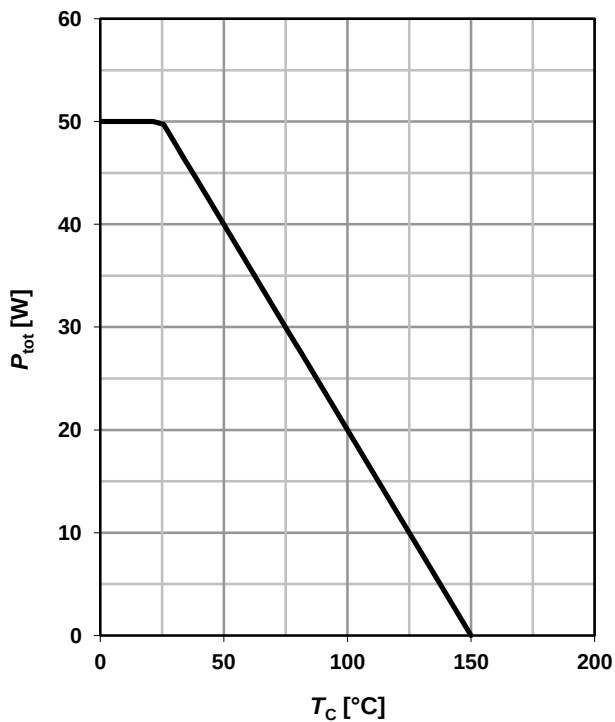
**Reverse Diode**

|                                  |               |                                                                           |   |      |     |    |
|----------------------------------|---------------|---------------------------------------------------------------------------|---|------|-----|----|
| Diode continuous forward current | $I_S$         | $T_C=25\text{ °C}$                                                        | - | -    | 53  | A  |
| Diode pulse current              | $I_{S,pulse}$ |                                                                           | - | -    | 212 |    |
| Diode forward voltage            | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=50\text{ A},$<br>$T_J=25\text{ °C}$               | - | 0.95 | 1.2 | V  |
| Reverse recovery time            | $t_{rr}$      | $V_R=30\text{ V}, I_F=50\text{ A},$<br>$di_F/dt=100\text{ A}/\mu\text{s}$ | - | 36   | -   | ns |
| Reverse recovery charge          | $Q_{rr}$      |                                                                           | - | 38   | -   | nC |

<sup>5)</sup> See figure 16 for gate charge parameter definition

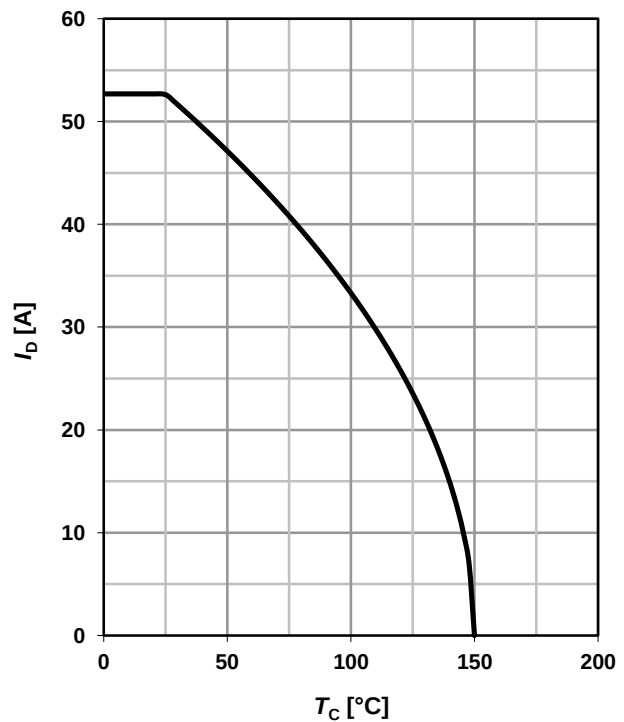
### 1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$



### 2 Drain current

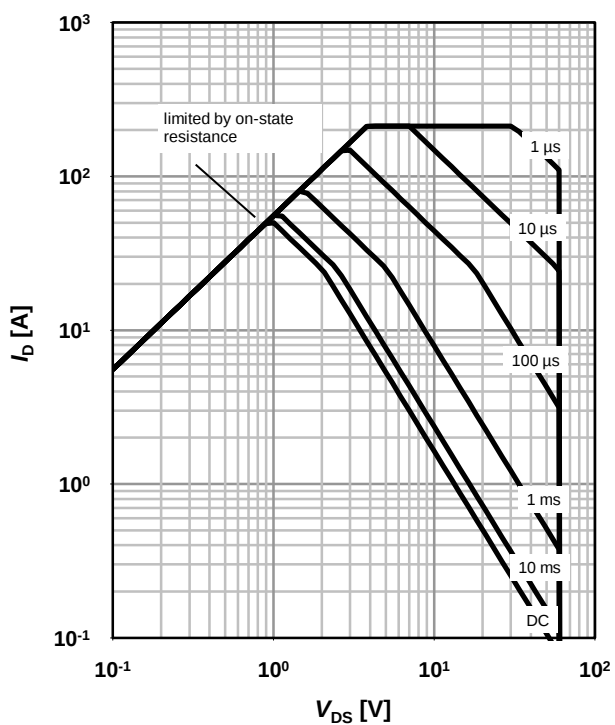
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$



### 3 Safe operating area

$$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0$$

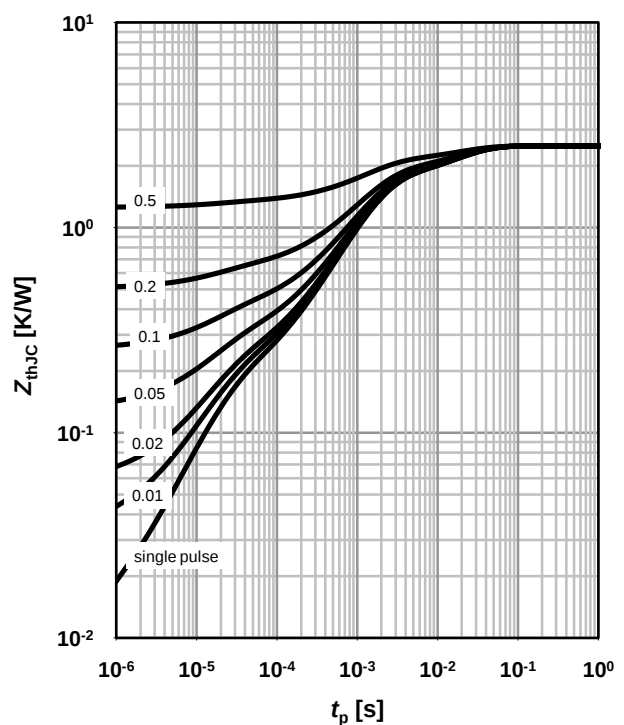
parameter:  $t_p$



### 4 Max. transient thermal impedance

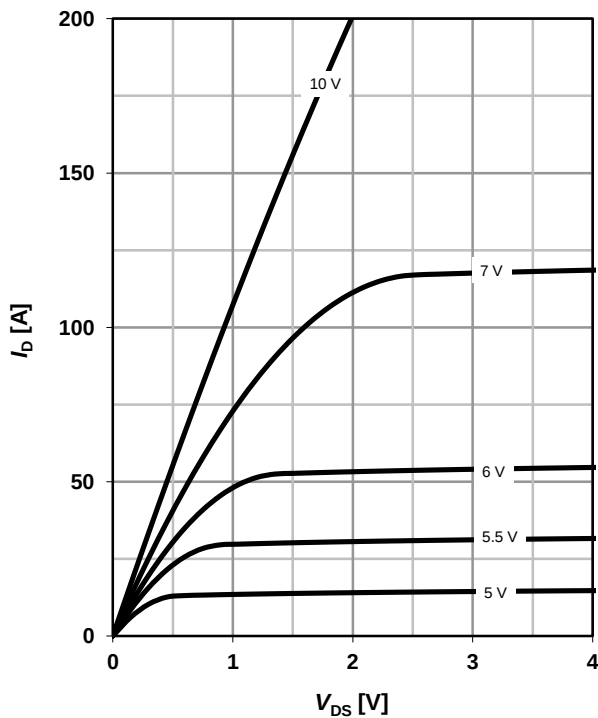
$$Z_{thJC} = f(t_p)$$

parameter:  $D = t_p / T$



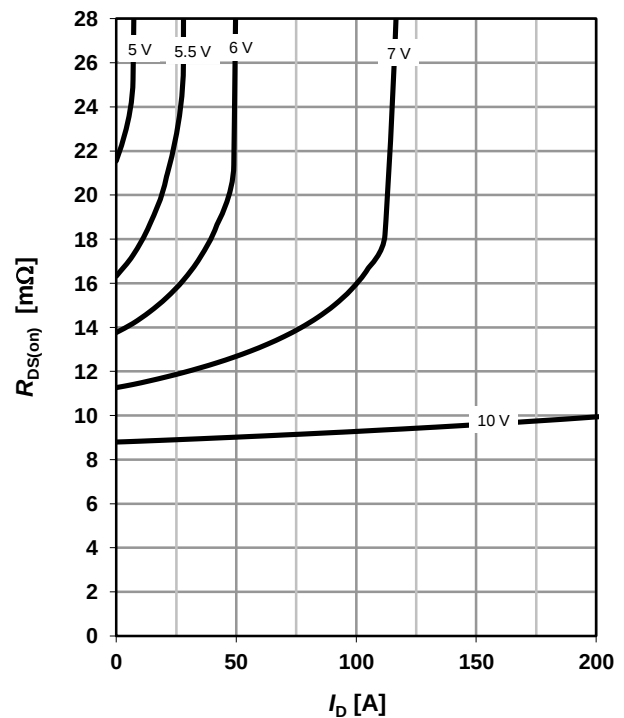
## 5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$ 

parameter:  $V_{GS}$ 


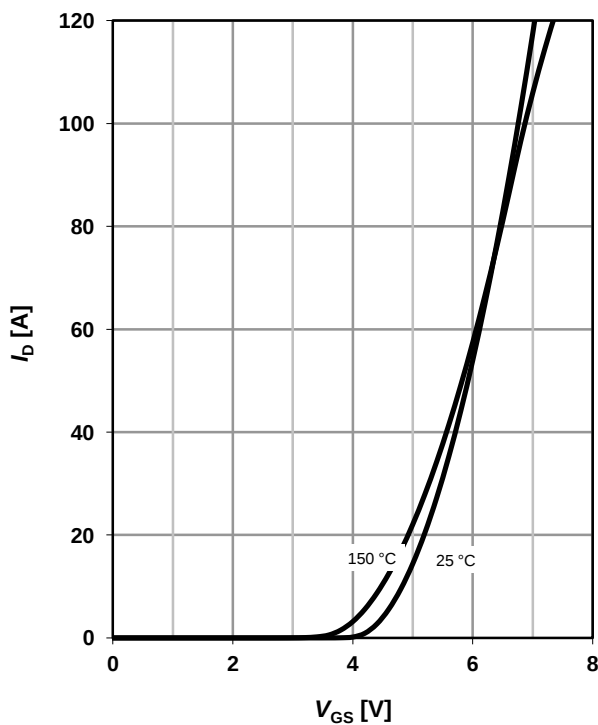
## 6 Typ. drain-source on resistance

 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$ 

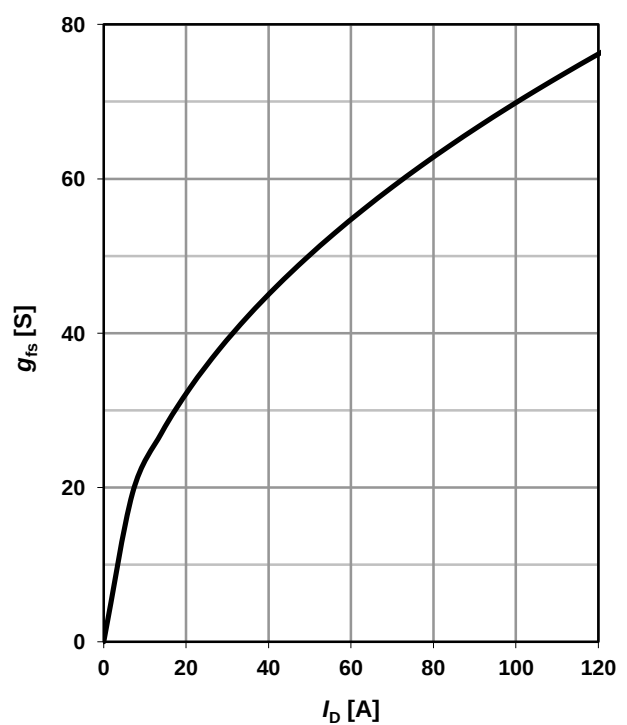
parameter:  $V_{GS}$ 


## 7 Typ. transfer characteristics

 $I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$ 

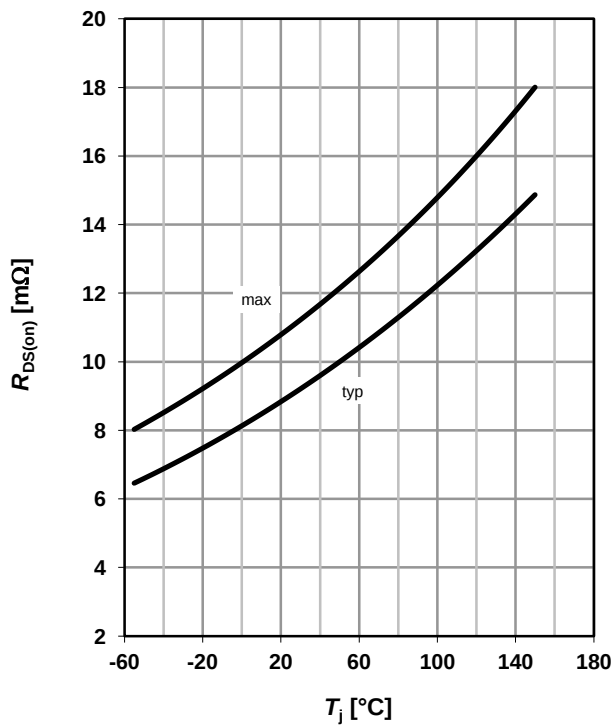
parameter:  $T_j$ 


## 8 Typ. forward transconductance

 $g_{fs} = f(I_D); T_j = 25^\circ\text{C}$ 


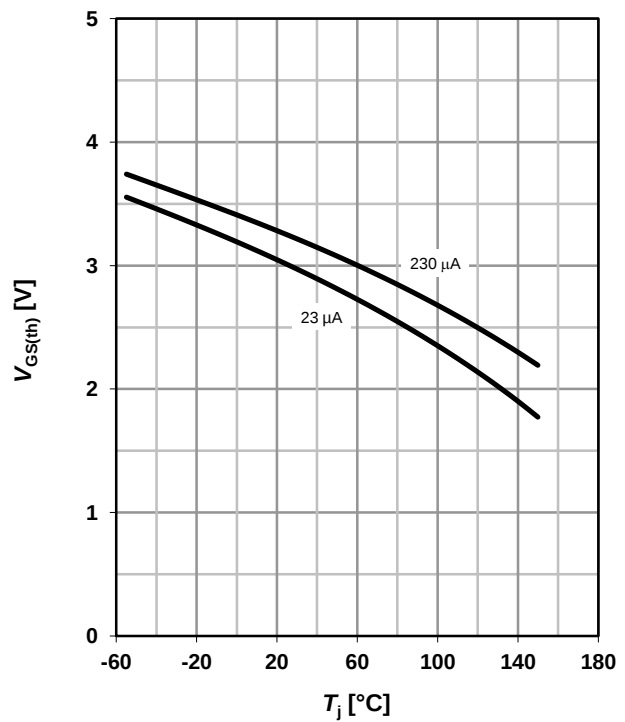
### 9 Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$ ;  $I_D = 50 \text{ A}$ ;  $V_{GS} = 10 \text{ V}$



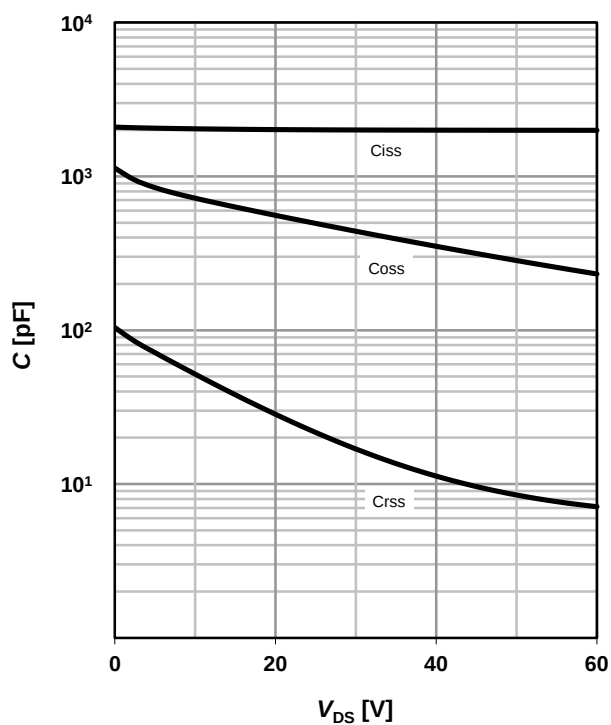
### 10 Typ. gate threshold voltage

$V_{GS(th)} = f(T_j)$ ;  $V_{GS} = V_{DS}$



### 11 Typ. capacitances

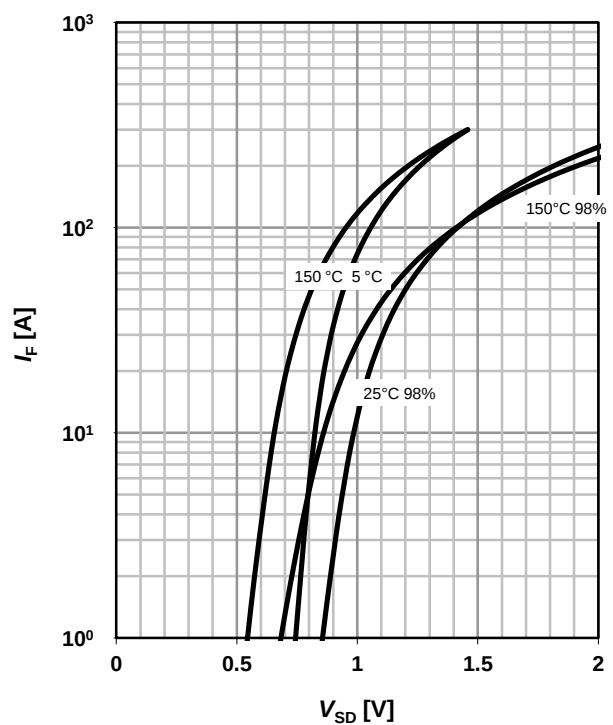
$C = f(V_{DS})$ ;  $V_{GS} = 0 \text{ V}$ ;  $f = 1 \text{ MHz}$



### 12 Forward characteristics of reverse diode

$I_F = f(V_{SD})$

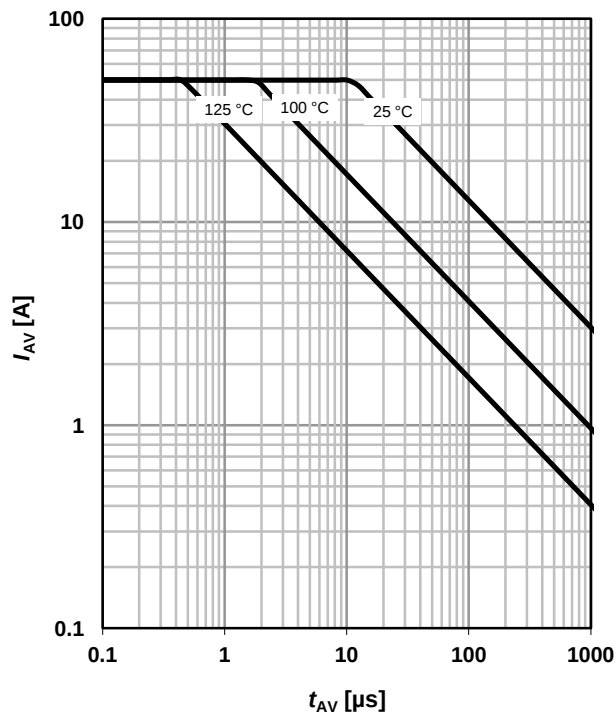
parameter:  $T_j$



### 13 Avalanche characteristics

$$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$$

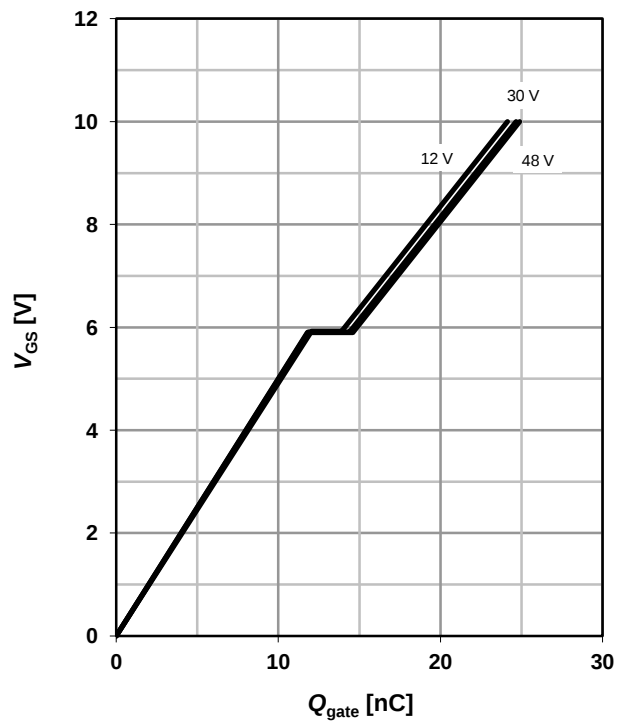
parameter:  $T_{j(\text{start})}$



### 14 Typ. gate charge

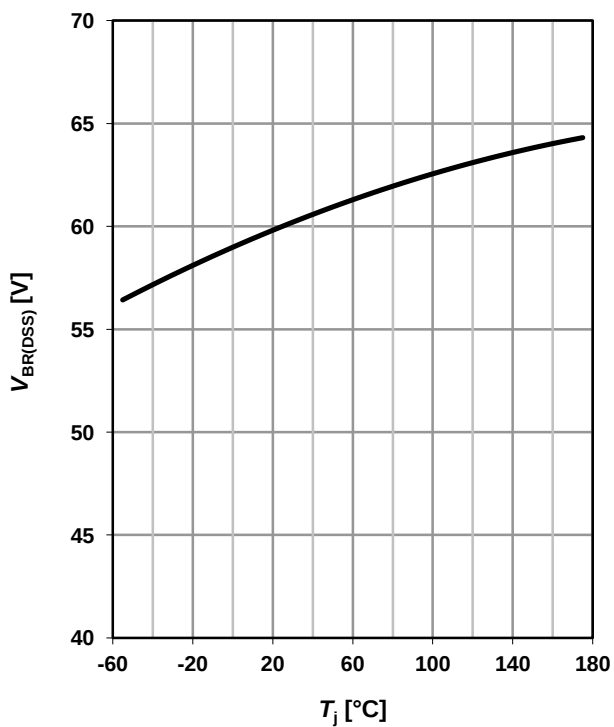
$$V_{GS}=f(Q_{\text{gate}}); I_D=50\ \text{A pulsed}$$

parameter:  $V_{DD}$



### 15 Drain-source breakdown voltage

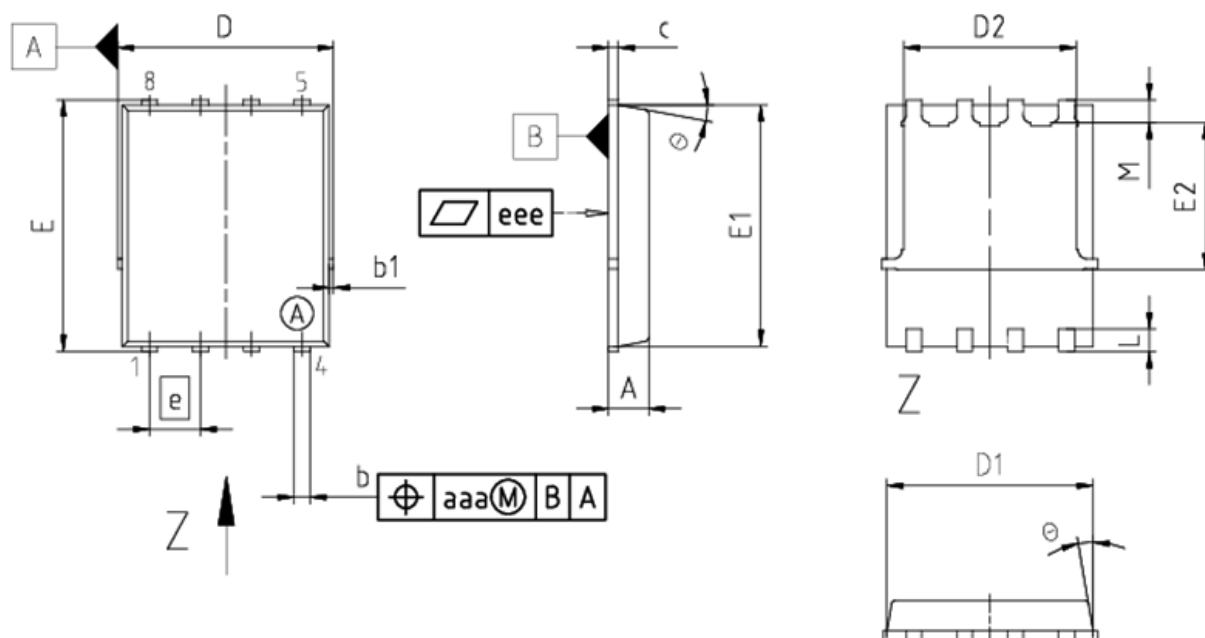
$$V_{BR(DSS)}=f(T_j); I_D=1\ \text{mA}$$



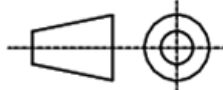
### 16 Gate charge waveforms



## PG-TDSON-8 (SuperSO8)



| DIM | MILLIMETERS |      |
|-----|-------------|------|
|     | MIN         | MAX  |
| A   | 0.90        | 1.10 |
| b   | 0.31        | 0.54 |
| b1  | 0.02        | 0.22 |
| c   | 0.15        | 0.35 |
| D   | 5.15        | 5.49 |
| D1  | 4.95        | 5.35 |
| D2  | 3.70        | 4.40 |
| E   | 5.95        | 6.35 |
| E1  | 5.70        | 6.10 |
| E2  | 3.40        | 3.80 |
| e   | 1.27        |      |
| N   | 8           |      |
| L   | 0.45        | 0.71 |
| M   | 0.45        | 0.75 |
| ø   | 8.5°        | 12°  |
| aaa | 0.25        |      |
| eee | 0.08        |      |

|                                                                                                              |
|--------------------------------------------------------------------------------------------------------------|
| DOCUMENT NO.<br>Z8B00003332                                                                                  |
| SCALE<br>0 2 4mm                                                                                             |
| EUROPEAN PROJECTION<br> |
| ISSUE DATE<br>10-04-2013                                                                                     |
| REVISION<br>04                                                                                               |

**Published by**  
**Infineon Technologies AG**  
**81726 Munich, Germany**  
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